

RL78/I1A

RENESAS MCU

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True Low Power Platform, High Resolution PWM and Rich Analog, 2.7 V to 5.5 V operation, 32 to 64 Kbyte Flash, for Inverter Control, Digital Power Control and Lighting Control Applications

1. OUTLINE

1.1 Features

Ultra-Low Power Technology

- 2.7 V to 5.5 V operation from a single supply
- Stop (RAM retained): 0.23 μA, (LVD enabled): 0.31 μA
- Halt (RTC + LVD): 0.60 μA
- Operating: 156.25 μA/MHz

16-bit RL78 CPU Core

- Delivers 41 DMIPS at maximum operating frequency of 32 MHz
- Instruction execution: 86% of instructions can be executed in 1 to 2 clock cycles
- CISC architecture (Harvard) with 3-stage pipeline
- Multiply signed & unsigned: 16 x 16 to 32-bit result in 1 clock cycle
- MAC: 16 x 16 to 32-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 1 clock cycle
- 1-wire on-chip debug function

Main Flash Memory

- Density: 32 KB to 64 KB
- Block size: 1 KB
- On-chip single voltage flash memory with protection from block erase/writing
- Self-programming with secure boot swap function and flash shield window function

Data Flash Memory

- Data flash with background operation
- Data flash size: 4 KB
- Erase cycles: 1 million (typ.)
- Erase/programming voltage: 2.7 V to 5.5 V

RAM

 $\langle R \rangle$

- 2 KB to 4 KB size options
- Supports operands or instructions
- Back-up retention in all modes

High-speed On-chip Oscillator

- 32 MHz with +/- 1% accuracy over voltage (2.7 V to 5.5 V) and temperature (-20°C to 85°C)
- Pre-configured settings: 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz & 1 MHz

Reset and Supply Management

- Power-on reset (POR) monitor/generator
- Low voltage detection (LVD) with 6 setting options (Interrupt and/or reset function)

Data Memory Access (DMA) Controller

- Up to 2 fully programmable channels
- Transfer unit: 8- or 16-bit

16-bit timers KB0 to KB2, and KC0 for PWM output

16-bit timers KB0 to KB2: maximum 6 outputs (3 channels × 2)

- Smooth start function, dithering function, forced output stop function (unsynchronized with comparator or external interrupt) enables over-voltage protection, over-current protection and peak current control, and single/interleave PFC function
- Average resolution < 0.98 nsec output, 64 MHz (when using PLL) + dithering option

16-bit timer KC0 (1 channel × 6 (output))

 PWM output gating function by interlocking with 16-bit timers KB0. KB1, and KB2

Extended-Function Timers

- Multi-function 16-bit timers: Up to 8 channels
- Real-time clock (RTC): 1 channel (full calendar and alarm function with watch correction function)
- Interval timer: 12-bit, 1 channel
- 15 kHz watchdog timer: 1 channel (window function)

Multiple Communication Interfaces

- Up to 1 channel x I²C multi-master (SMBus/PMBus support)
- Up to 1 channel x Simplified SPI (CSINote1)/SPI (7-, 8bit)
- Up to 3 channels x UART (7-, 8-, 9-bit),
 DALI support 1 channel (8-, 16-, 17-, 24-bit, master and slave)
- Up to 1 channel x LIN

Rich Analog

- \bullet ADC: Up to 11 channels, 8/10-bit resolution, 2.125 $\mu \rm s$ conversion time
- Supports 2.7 V
- Internal voltage reference (1.45 V)
- Comparator: High response time 70 ns (typ.), up to 6 channels, internal DAC 3 channels 8-bit resolution, window comparator mode
- PGA (x4 to x32): 6 input channels
- On-chip temperature sensor

Safety Features (IEC or UL 60730 compliance)

- Flash memory CRC calculation
- RAM parity error check
- RAM/SFR write protection
- Illegal memory access detection
- Clock stop/frequency detection
- ADC self-test

General Purpose I/O

- 5-V tolerant, high-current (up to 8.5 mA per pin)
- Open-drain, internal pull-up support

Operating Ambient Temperature

- Standard: -40°C to +105°C
- Extend: -40°C to +125°C

Package Type and Pin Count

SSOP: 20, 30, 38



Notes 1. Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.

o ROM, RAM capacities

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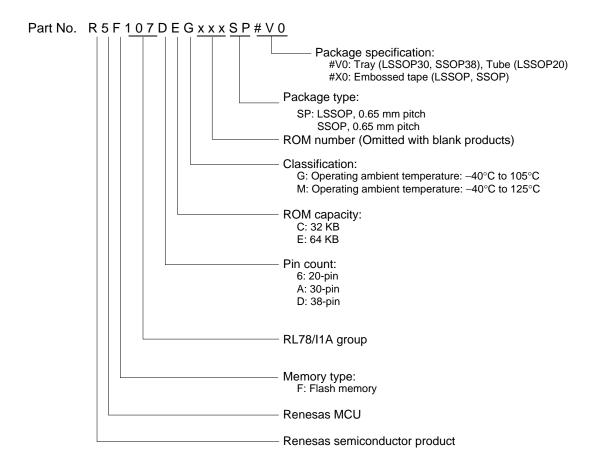
Flash ROM	Data flash	RAM	RL78/I1A				
			20 pins	30 pins	38 pins		
64 KB	4 KB	4 KB Note	ı	R5F107AE	R5F107DE		
32 KB	4 KB	2 KB	R5F1076C	R5F107AC	-		

Note This is about 3 KB when the self-programming function and data flash function are used.



1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/I1A



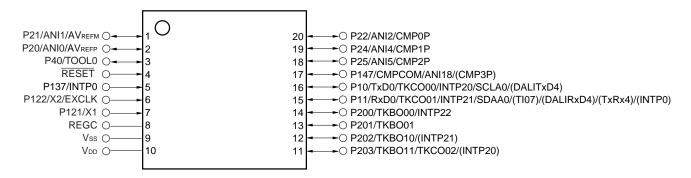
Pin count	Package	Operating Ambient Temperature	Part Number
20 pins	20-pin plastic LSSOP	$T_A = -40 \text{ to } +105^{\circ}\text{C}$	R5F1076CGSP#V0, R5F1076CGSP#X0
	(4.4 × 6.5)	T _A = -40 to +125°C	R5F1076CMSP#V0, R5F1076CMSP#X0
30 pins	30-pin plastic LSSOP (7.62 mm (300))	$T_A = -40 \text{ to } +105^{\circ}\text{C}$	R5F107ACGSP#V0, R5F107AEGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#X0
		T _A = -40 to +125°C	R5F107ACMSP#V0, R5F107AEMSP#V0, R5F107ACMSP#X0, R5F107AEMSP#X0
38 pins	38-pin plastic SSOP	Ta = -40 to +105°C	R5F107DEGSP#V0, R5F107DEGSP#X0
	(7.62 mm (300))	Ta = -40 to +125°C	R5F107DEMSP#V0, R5F107DEMSP#X0

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

• 20-pin plastic LSSOP (4.4 x 6.5)

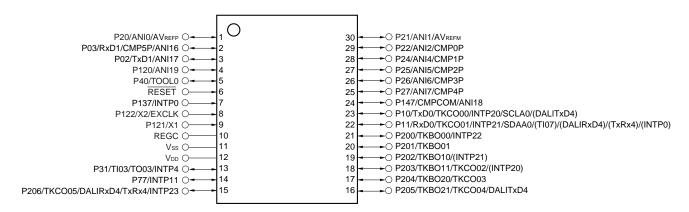


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.
 - **3.** The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).

1.3.2 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300))

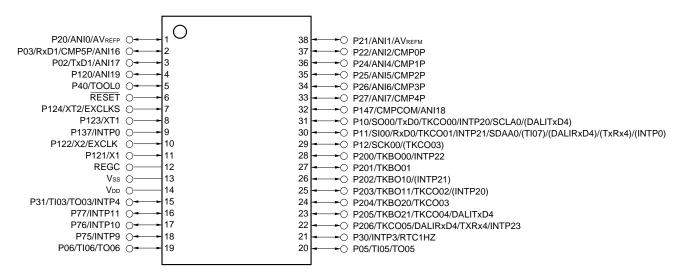


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

1.3.3 38-pin products

• 38-pin plastic SSOP (7.62 mm (300))



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

1.4 Pin Identification

ANI0 to ANI2, REGC: Regulator Capacitance

ANI4 to ANI7, RESET: Reset

ANI16 to ANI19: Analog Input RTC1HZ: Real-time Clock Correction Clock

AVREFM: Analog Reference Voltage Minus (1 Hz) Output

AVREFP: Analog Reference Voltage Plus RxD0, RxD1,

CMP0P to CMP5P: Comparator Analog Input DALIRxD4: Receive Data

CMPCOM: Comparator External Reference SCK00: Serial Clock Input/Output

Voltage SCLA0: Serial Clock Input/Output

EXCLK: External Clock Input (Main System SDAA0: Serial Data Input/Output

Clock) SI00: Serial Data Input

EXCLKS: External Clock Input (Subsystem SO00: Serial Data Output

Clock) TI03, TI05, TI06,

INTP0, INTP3, Timer Input

INTP4, INTP9, T003, T005, T006, INTP10, INTP11, TKB000, TKB001 to

INTP20 to INTP23: Interrupt Request from Peripheral TKBO20, TKBO21,

P02, P03, TKCO00 to TKCO05: Timer Output

P05, P06: Port 0 TOOL0: Data Input/Output for Tool

P10 to P12: Port 1 TxRx4: Serial Data Input/Output for Single

P20 to P22, Wired UART

P24 to P27: Port 2 TxD0, TxD1

Port 20

P30, P31: Port 3 DALITxD4: Transmit Data
P40: Port 4 VDD: Power Supply

P75 to P77: Port 7 Vss: Ground

P120 to P124: Port 12 X1, X2: Crystal Oscillator (Main System Clock)

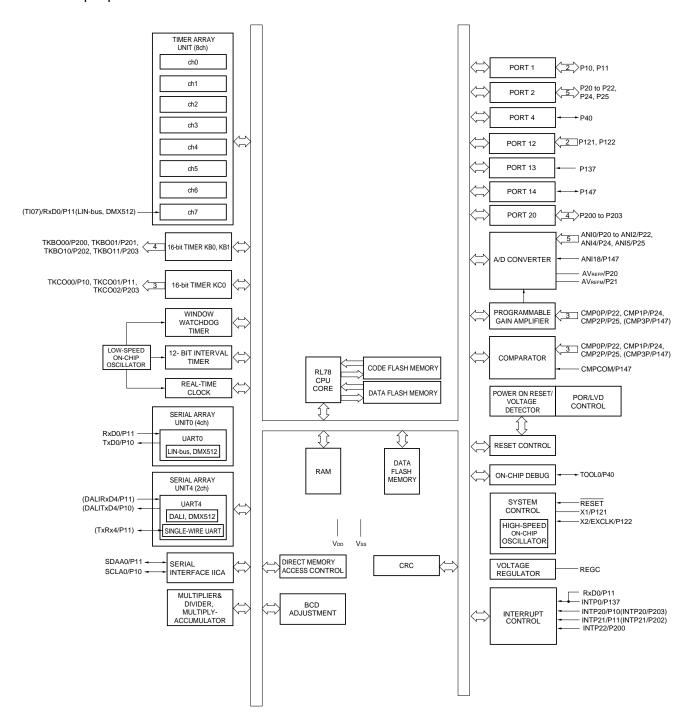
P137: Port 13 XT1, XT2: Crystal Oscillator (Subsystem Clock)

P147: Port 14

P200 to P206:

1.5 Block Diagram

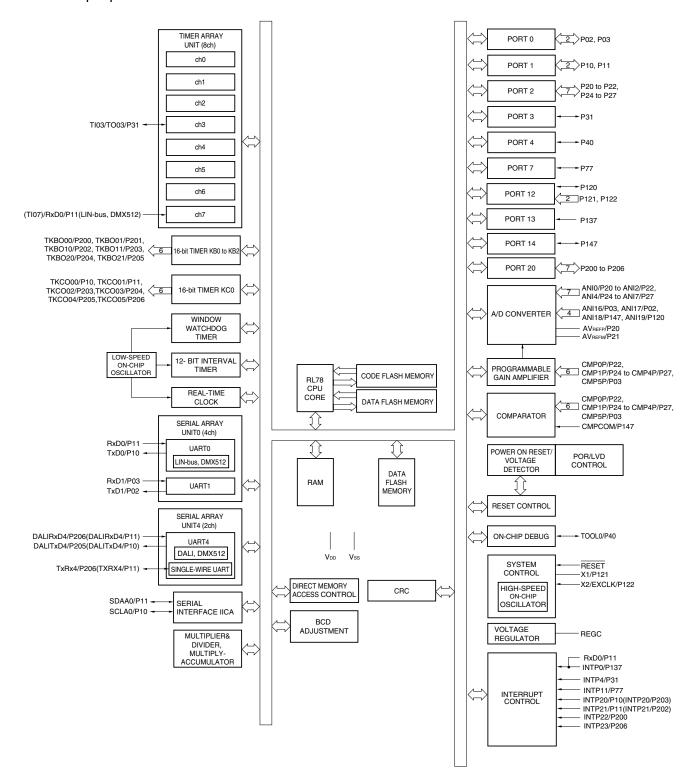
1.5.1 20-pin products



Remarks 1. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

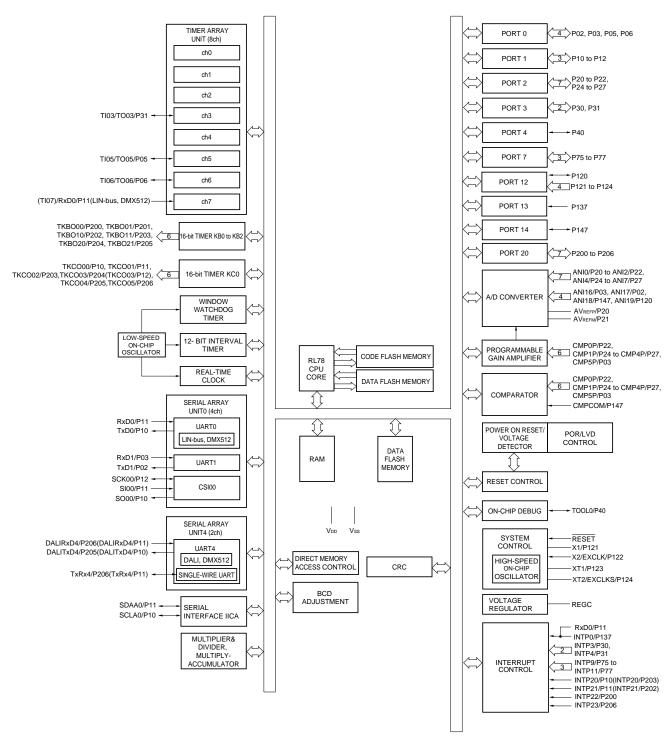
2. The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).

1.5.2 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

1.5.3 38-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

1.6 Outline of Functions

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR1) is set to 00H.

(1/3)

					(1/0)				
	Item	20-pin	30-	pin	38-pin				
		R5F1076C	R5F107AC	R5F107AE	R5F107DE				
Code flash m	emory (KB)	32	32	64	64				
Data flash me	emory (KB)	4	4	4	4				
RAM (KB)		2	2	4 ^{Note 1}	4 ^{Note 1}				
Address space	е	1 MB							
Main system clock	High-speed system clock	HS (High-speed main)	cillation, external main symmode: 1 to 20 MHz (V_{DD} = node: 1 to 8 MHz (V_{DD} =	•					
	High-speed on-chip oscillator		mode: 1 to 32 MHz (V_{DD} = node: 1 to 8 MHz (V_{DD} =	•					
Clock for 16-b and KC0	oit timers KB0 to KB2,	64 MHz (TYP.)							
Subsystem clock (38-pin products only)		XT1 (crystal) oscillation 32.768 kHz	XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz						
Low-speed or	n-chip oscillator	15 kHz (TYP.)							
General-purp	ose register	(8-bit register × 8) × 4 banks							
Minimum inst	ruction execution time	$0.03125 \mu s$ (High-speed on-chip oscillator: f_{H} = 32 MHz operation)							
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)							
		30.5 μ s (Subsystem clock: f _{SUB} = 32.768 kHz operation) (38-pin products only)							
Instruction se	t	 8-bit operation, 16-bit operation Multiplication (8 bits × 8 bits) Bit manipulation (Set, reset, test, and Boolean operation), etc. 							
I/O port	Total	16	2	26	34				
	CMOS I/O	13	2	23	29				
	CMOS input	3	;	3	5				
	CMOS output	-	-	-	_				
Timer	16-bit timer TAU	8 channels (no timer output)	8 channels (timer output	: 1, PWM output: 1 ^{Note 2})	8 channels (timer outputs: 3, PWM outputs: 3 ^{Note 2})				
	16-bit timer KB	2 channels (PWM outputs: 6) outputs: 4)							
	16-bit timer KC	1 channel (PWM outputs: 3)	1 channel (PWM outputs: 6)						

- **Notes 1.** This is about 3 KB when the self-programming function and data flash function are used. (For details, see **CHAPTER 3 in the RL78/I1A User's Manual**.)
 - The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/I1A User's Manual).

(2/3)

					(2/3)				
	Item		20-pin	30-pin	38-pin				
			R5F1076C	R5F107AC, R5F107AE	R5F107DE				
Timer	Watchdo	g timer		1 channel					
	Real-time	e clock		1 channel ^{Notes 1, 2}					
	12-bit inte	erval timer		1 channel					
	RTC outp	out		-	1 1 Hz (subsystem clock fsub = 32.768 kHz)				
8/10-bit resoluti	on A/D c	onverter	6 channels	11 channels	11 channels				
Comparator			4 channels	6 channels	6 channels				
Programmable	gain amp	lifier		1 channel					
		Input ^{Note 3}	4 channels	6 channels	6 channels				
Serial interface		1	[20-pin] Note 5		•				
				N-bus and DMX512): 1 channel					
			UART (Supporting DALI communication): 1 channel						
			[30-pin products]						
			UART (Supporting LIN-bus and DMX512): 1 channel						
			• UART: 1 channel						
			UART (Supporting DALI communication): 1 channel						
			[38-pin products] • Simplified SPI (CSI): 1 channel/UART (Supporting LIN-bus and DMX512): 1 channel • UART: 1 channel						
			UART (Supporting DA	ALI communication): 1 channel	T				
	I ² C b	us	1 channel	1 channel	1 channel				
Multiplier and d accumulator	vider/mu	Itiply-	 • 16 bits × 16 bits = 32 bits (Unsigned or signed) • 32 bits ÷ 32 bits = 32 bits (Unsigned) • 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 						
DMA controller				2 channels					
Vectored interru	ıpt Inter	nal	27	30	30				
sources	Exte	rnal	7	10	11				
Reset	•		Reset by RESET pin						
			Internal reset by watchdog timer						
			Internal reset by power-on-reset						
			Internal reset by volta	age detector al instruction execution ^{Note 4}					
			Internal reset by filega Internal reset by RAM						
			Internal reset by Ivania parity error Internal reset by illegal-memory access						

Notes 1. The subsystem clock (fsub) can be selected as the operating clock only for 38-pin products.

- 2. The 20- and 30-pin products can only be used as the constant-period interrupt function.
- 3. The comparator input is alternatively used with analog input pin (ANI pin).
- 4. The illegal instruction is generated when instruction code FFH is executed.
 Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.
- 5. The 20 pin products can only be used 1 UART simultaneously due to sharing of the same I/O pins.





(3/3)

			(0/0)			
Item	20-pin	30-pin	38-pin			
	R5F1076C	R5F107AC, R5F107AE	R5F107DE			
Power-on-reset circuit		Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.)				
Voltage detector	= =	\$ \$ '				
On-chip debug function	Provided					
Power supply voltage	V _{DD} = 2.7 to 5.5 V					
Operating ambient temperature	$T_A = -40 \text{ to } +105^{\circ}\text{C}$ (G: Industrial applications), $T_A = -40 \text{ to } +125^{\circ}\text{C}$ (M: Industrial applications)					

2. ELECTRICAL SPECIFICATIONS

(G: Industrial applications, $T_A = -40$ to +105°C)

In this chapter, shows the electrical specifications of the target products.

Target products (G: Industrial applications): $T_A = -40 \text{ to } + 105^{\circ}\text{C}$ R5F107xxGxx

- Cautions 1. The RL78/I1A has an on-chip debug function, which is provided for development and evaluation.

 Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 Functions for each product in the RL78/I1A User's Manual.



2.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		–0.5 to +6.5	٧
REGC pin input voltage	Virego	REGC	−0.3 to +2.8 and −0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VII	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-0.3 to V _{DD} +0.3 ^{Note 2}	٧
Analog input voltage	Vai1	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	٧

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **2.** $AV_{REF(+)}$: + side reference voltage of the A/D converter.
- 3. Vss: Reference voltage

Absolute Maximum Ratings ($T_A = 25$ °C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40	mA
		Total of all pins	P02, P03, P40, P120	-70	mA
		–170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	Iон ₂	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins 170 mA	P02, P03, P40, P120	70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	lo _{L2}	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operation	on mode	-40 to +105	°C
temperature		In flash memory programming mode			
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/crystal resonator		1.0		20.0	MHz
XT1 clock oscillation frequency (fxt)Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. See **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, see **5.4 System Clock Oscillator in the RL78/I1A**User's Manual.

2.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Note 1}	fін		1		32	MHz
High-speed on-chip oscillator		T _A = -20 to 85°C	-1		+1	%
clock frequency accuracyNote 2		T _A = -40 to 105°C	-1.5		+1.5	%
Low-speed on-chip oscillator clock frequency	fıL			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - 2. This indicates the oscillator characteristics only. See AC Characteristics for instruction execution time.

2.2.3 PLL characteristics

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	f _{PLLIN}	High-speed system clock is selected (f _{MX} = 4 MHz)	3.94	4.00	4.06	MHz
frequency ^{Note}		High-speed on-chip oscillator clock is selected (f _{IH} = 4 MHz)	3.94	4.00	4.06	MHz
PLL output clock frequency ^{Note}	f _{PLL}			fpllin × 16		MHz

Note This only indicates the oscillator characteristics. See AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	І он1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~V \leq V_{DD} \leq 5.5~V$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-1.0	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			-12.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-4.0	mA
		Total of P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206 (When duty $\le 70\%^{\text{Note 3}}$) Total of all pins (When duty $\le 70\%^{\text{Note 3}}$)	$4.0~V \leq V_{DD} \leq 5.5~V$			-30.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-10.0	mA
			$4.0~V \leq V_{DD} \leq 5.5~V$			-30.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-14.0	mA
Іон2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			-0.1 ^{Note 2}	mA	
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.7~V \leq V_{DD} \leq 5.5~V$			-0.7	mA

- **Notes 1.** Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - **2.** However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and I_{OH} = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	l _{OL1}	Per pin for P02, P03, P05, P06,	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			8.5 ^{Note 2}	mA
IOW ^{Note 1}		P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			1.5 ^{Note 2}	mA
		Total of P02, P03, P40, P120 (When duty \leq 70% Note 3) Total of P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206 (When duty \leq 70% Note 3)	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			7.5	mA
			$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			17.5	mA
		Total of all pins	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			80.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			25.0	mA
	lo _{L2}	Per pin for P20 to P22, P24 to P27	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			0.4 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$			2.8	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoL × 0.7)/(n × 0.01)

<Example> Where n = 80% and IoL = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0.8V _{DD}		V _{DD}	٧
	V _{IH2}	P03, P10, P11	TTL input buffer $4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	2.1		V _{DD}	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}$	2.0		V _{DD}	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		V _{DD}	V
Input voltage, low	VIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	V
	V _{IL2}	P03, P10, P11	TTL input buffer 4.0 V ≤ V _{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ V _{DD} < 4.0 V	0		0.5	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	0		0.32	V

Caution The maximum value of VIH of pins P02, P10 to P12 is VDD, even in the N-ch open-drain mode.

(Ta = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high			$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -3.0 \text{ mA}$	V _{DD} - 0.7			V
		P200 to P206	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OH1}} = -1.0 \text{ mA}$	V _{DD} - 0.5			V
	V _{OH2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \ \mu\text{A}$	V _{DD} - 0.5			V
Output voltage, low			$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 8.5 \text{ mA}$			0.7	V
		P31, P40, P75 to P77, P120, P147, P200 to P206	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 4.0 \text{ mA}$			0.4	V
			$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 1.5 \text{ mA}$			0.4	V
	V _{OL2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL2} = 400 \ \mu\text{A}$			0.4	V

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Condition	าร		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ілін1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	V _I = V _{DD}				1	μΑ
	ILIH2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	$V_{I} = V_{DD}$	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
Input leakage current, low						-1	μA	
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pull-up resistance	R∪	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	Vı = Vss, In	input port	10	20	100	kΩ

2.3.2 Supply current characteristics

(T_A = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, Vss = 0 V) (1/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	f _{IH} = 32 MHz ^{Note 3}	V _{DD} = 5.0 V		5.0	7.5	mA
current Note 1		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		5.0	7.5	mA
			mode ***	f _{IH} = 24 MHz ^{Note 3}	V _{DD} = 5.0 V		3.9	5.8	mA
					V _{DD} = 3.0 V		3.9	5.8	mA
				f _{IH} = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.2	mA
					V _{DD} = 3.0 V		2.9	4.2	mA
			LS (low- speed main) mode ^{Note 5}	f _{IH} = 8 MHz ^{Note 3} , TA = -40 to + 85°C	V _{DD} = 3.0 V		1.3	2.0	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	4.9	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	Resonator connection		3.3	5.0	mA
			mode	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	4.9	mA
				V _{DD} = 3.0 V	Resonator connection		3.3	5.0	mA
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	2.9	mA
			V _{DD} = 5.0 V	Resonator connection		2.0	2.9	mA	
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	2.9	mA
			V _{DD} = 3.0 V	Resonator connection		2.0	2.9	mA	
			LS (low-	main) $V_{DD} = 3.0 \text{ V},$ $T_{A} = -40 \text{ to } + 85^{\circ}\text{C}$	Square wave input		1.2	1.8	mA
			speed main) mode ^{Note 5}		Resonator connection		1.2	1.8	mA
			HS (high- f _{IH} = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		5.4	8.5	mA	
			speed main) mode ^{Note 5}				5.4	8.5	mA
			mode	f _{IH} = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		3.3	5.7	mA
				fpll = 64 MHz, fclk = 16 MHz	V _{DD} = 3.0 V		3.3	5.7	mA
			Subsystem	fsub = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μА
			clock operation	T _A = -40°C	Resonator connection		4.4	6.2	μА
			operation	fsub = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μΑ
				T _A = +25°C	Resonator connection		4.4	6.2	μА
				fsub = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μА
				T _A = +50°C	Resonator connection		4.5	7.4	μΑ
				fsub = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μА
		T _A = +70°C	Resonator connection		4.6	8.3	μА		
		f _{SUB} = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μA		
			T _A = +85°C	Resonator connection		5.4	11.6	μA	
		f _{SUB} = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μA		
				T _A = +105°C	Resonator connection		7.1	21.0	μA

(Notes and Remarks are listed on the next page.)

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- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main), and LS (low-speed main) modes
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten. In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1}$ MHz to 32 MHz LS (low-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1}$ MHz to 8 MHz

- **Remarks 1.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(Ta = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, Vss = 0 V) (2/2)

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Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	1		HS (high-	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.72	2.9	mA
current		mode	speed main)		V _{DD} = 3.0 V		0.72	2.9	mA
Note 1			mode ^{Note 6}	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.57	2.3	mA
					V _{DD} = 3.0 V		0.57	2.3	mA
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	1.7	mA
					V _{DD} = 3.0 V		0.50	1.7	mA
			LS (low- speed main) mode ^{Note 6}	f _{IH} = 8 MHz ^{Note 4} , T _A = -40 to +85°C	V _{DD} = 3.0 V		320	910	μА
			HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	1.9	mA
			speed main)	V _{DD} = 5.0 V	Resonator connection		0.50	2.0	mA
			mode	ode ^{Note 6} $f_{MX} = 20 \text{ MHz}^{\text{Note 3}}, \qquad S$			0.40	1.9	mA
				V _{DD} = 3.0 V	Resonator connection		0.50	2.0	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.02	mA
				V _{DD} = 5.0 V	Resonator connection		0.30	1.08	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.02	mA
			V _{DD} = 3.0 V	Resonator connection		0.30	1.08	mA	
			LS (low-	<u> </u>	Square wave input		130	720	μΑ
	speed main) mode ^{Note 6}	$V_{DD} = 3.0 \text{ V},$ $T_A = -40 \text{ to } +85^{\circ}\text{C}$	Resonator connection		170	760	μΑ		
			HS (high-	ain) fpll = 64 MHz, fclk = 32 MHz	V _{DD} = 5.0 V		1.15	4.0	mA
			speed main) mode ^{Note 6}		V _{DD} = 3.0 V		1.15	4.0	mA
			mode		V _{DD} = 5.0 V		0.95	3.2	mA
					V _{DD} = 3.0 V		0.95	3.2	mA
			Subsystem	f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.70	μΑ
			clock	T _A = -40°C	Resonator connection		0.47	0.89	μΑ
			operation	f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.33	0.70	μΑ
				T _A = +25°C	Resonator connection		0.52	0.89	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.41	1.90	μΑ
				T _A = +50°C	Resonator connection		0.60	2.09	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		0.54	2.80	μΑ
				T _A = +70°C	Resonator connection		0.73	2.99	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		1.27	6.10	μΑ
				T _A = +85°C	Resonator connection		1.46	6.29	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		3.04	15.5	μΑ
				T _A = +105°C	Resonator connection		3.23	15.7	μΑ
	IDD3	STOP	T _A = -40°C				0.18	0.50	μΑ
		mode Note 7	T _A = +25°C				0.23	0.50	μΑ
			T _A = +50°C				0.27	1.70	μΑ
			T _A = +70°C				0.44	2.60	μΑ
			T _A = +85°C				1.17	5.90	μΑ
			T _A = +105°C				2.94	15.3	μΑ

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(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main) and LS (low-speed main) modes
 - •The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - •The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.

In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- 4. When high-speed system clock and subsystem clock are stopped.
- **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1}$ MHz to 32 MHz LS (low-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1}$ MHz to 8 MHz

- 7. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C



(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

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Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	IFIL Note 1						0.20		μΑ
RTC operating current	RTC Notes 1, 2, 3						0.02		μА
12-bit interval timer operating current	I _{IT} Notes 1, 2, 4						0.02		μA
Watchdog timer operating current	Notes 1, 2, 5	fı∟ = 15 kHz		<u>, </u>			0.22		μА
A/D converter operating current	IADC Notes 1, 6	When conversion maximum speed			$AV_{REFP} = V_{DD} = 5.0 \text{ V}$ node, $AV_{REFP} = V_{DD} = 3.0 \text{ V}$		1.3 0.5	1.7 0.7	mA mA
A/D converter reference voltage current	IADREF ^{Note 1}			Low voltage in	000, 744KET		75.0	0.7	μA
Temperature sensor operating current	I _{TMPS} Note 1						75.0		μА
LVD operating current	I _{LVD} Notes 1, 7						0.08		μΑ
Self- programming operating current	_{FSP} Notes 1, 8						2.50	12.2	mA
Programmable gain amplifier operating current	I _{PGA} Note 9				$AV_{REFP} = V_{DD} = 5.0 \text{ V}$ $AV_{REFP} = V_{DD} = 3.0 \text{ V}$		0.21	0.31	mA mA
Comparator	ICMPNote 10	When one comp	parator	channel is	AV _{REFP} = V _{DD} = 5.0 V		41.4	62	μА
operating current		operating			AV _{REFP} = V _{DD} = 3.0 V		37.2	59	μA
	IVREF	When one interr		erence voltage	AV _{REFP} = V _{DD} = 5.0 V		14.8	26	μА
		circuit is operation	ng		AV _{REFP} = V _{DD} = 3.0 V		8.9	20	μA
Programmable	IREF Note 11				AV _{REFP} = V _{DD} = 5.0 V		3.2	5.1	μA
gain amplifier/ comparator reference current source					AV _{REFP} = V _{DD} = 3.0 V		2.9	4.9	μΑ
BGO operating current	I _{BGO} Note 12						2.50	12.2	mA
SNOOZE	ISNOZ ^{Note 1}	ADC operation	The I	mode is perform	ed ^{Note 13}		0.50	1.1	mA
operating current					operations are performed, EFP = VDD = 5.0 V		2.0	3.04	mA
		Simplified SPI (0	CSI)/U	ART operation			0.70	1.54	mA

(Notes and Remarks are listed on the next page.)

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- Notes 1. Current flowing to the VDD.
 - 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - **4.** Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and fill operating current). The current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode.
 - **5.** Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
 - **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
 - 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
 - **8.** Current flowing during self-programming operation.
 - **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
 - **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
 - **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
 - **12.** Current flowing only during data flash rewrite.
 - 13. See 21.3.3 SNOOZE mode in the RL78/I1A User's Manual for shift time to the SNOOZE mode .
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$
 - 5. Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AVREFP = VDD = 5.0 V)

```
ICMP × 3 + IVREF + IPGA + IREF
= 41.4 [\mu A] × 3 + 14.8 [\mu A] × 1 + 210 [\mu A] + 3.2 [\mu A]
= 352.2 [\mu A]
```

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AVREFP = VDD = 5.0 V)

```
ICMP × 2 + IIREF
= 41.4 [\mu A] × 2 + 3.2 [\mu A]
= 86.0 [\mu A]
```

2.4 AC Characteristics

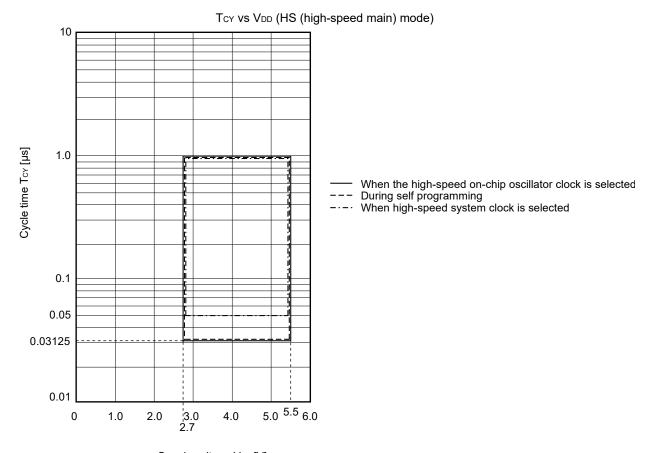
(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main system	HS (high-spe	eed m	nain) mode	0.03125		1	μS
instruction execution time)		clock (fmain) operation	LS (low-spee		$T_A = -40 \text{ to } +85^{\circ}\text{C}$	0.125		1	μS
		Subsystem clo	ck (fsuв) ор	eratio	on	28.5	30.5	31.3	μS
		In the self	HS (high-spe	eed m	nain) mode	0.03125		1	μS
		programming mode			0.125		1	μS	
External system clock frequency	fex				1.0		20.0	MHz	
	fexs					32		35	kHz
External system clock input high-	texh, texl					24			ns
level width, low-level width	texhs, texhs					13.7			μS
TI03, TI05, TI06, TI07 input high-level width, low-level width	tтıн, tтı∟					2/fмск+10			ns
TO03, TO05, TO06, TKBO00,	f то	HS (high-speed	d main)	4.0	$V \leq V_{DD} \leq 5.5~V$			8	MHz
TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to		mode		2.7	$V \le V_{DD} \le 4.0 V$			4	MHz
TKCO05 output frequency (When duty = 50%)		LS (low-speed		4.0	$V \leq V_{DD} \leq 5.5~V$			4	MHz
(When duty = 50%)		mode, $T_A = -40$	0 to +85°C	2.7	$V \le V_{DD} \le 4.0 V$			2	MHz
Interrupt input high-level width, low-level width	tinth, tintl	, ,	INTP0, INTP3, INTP4, INTP9 to INTP11, INTP20 to INTP23		1			μS	
RESET low-level width	trsl					10			μS

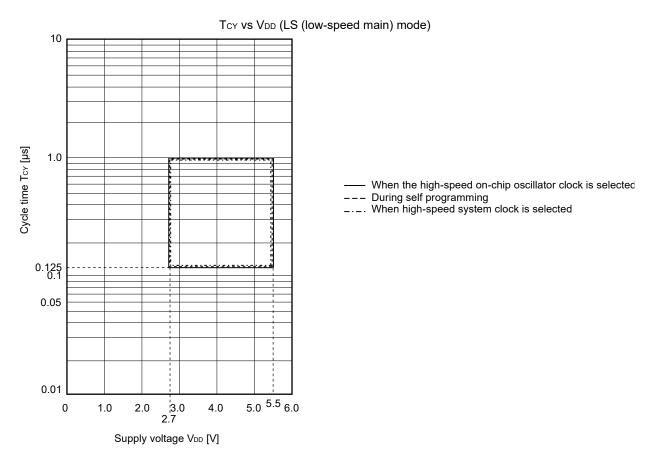
Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

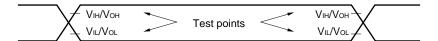
Minimum Instruction Execution Time during Main System Clock Operation



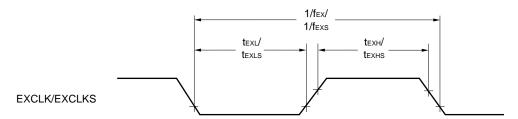




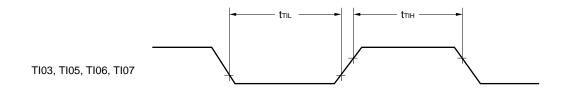
AC Timing Test Points

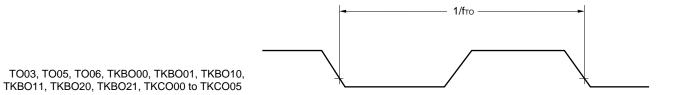


External System Clock Timing

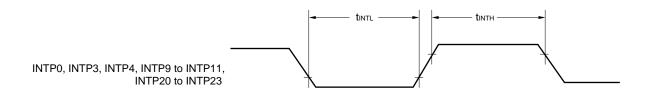


TI/TO Timing

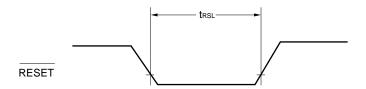




Interrupt Request Input Timing

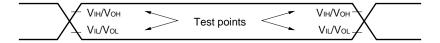


RESET Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

(1) During communication at same potential (UART mode) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate ^{Note 1}		2.7 V≤ V _{DD} ≤ 5.5 V			fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		5.3		1.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

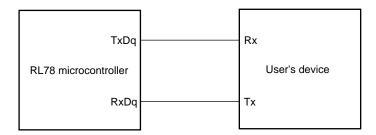
2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

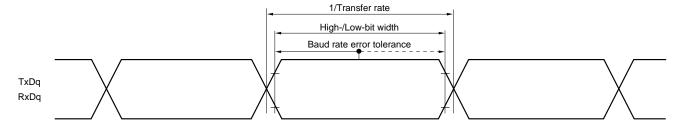
LS (low-speed main) mode: $8 \text{ MHz} (2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}), \text{ T}_{A} = -40 \text{ to } +85^{\circ}\text{C}$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03))

(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +105^{\circ}C^{\text{Note } 5}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-s _l	'	LS (low-sp	Unit	
			MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t KCY1	tkcy1 ≥ 4/fclk	125		500		ns
SCKp high-/low-level	t кн1,	$4.0~V \leq V_{DD} \leq 5.5~V$	tkcy1/2 - 12		tkcy1/2 - 50		ns
width	t _{KL1}	$2.7~V \leq V_{DD} \leq 5.5~V$	tkcy1/2 - 18		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑)	tsıĸ1	$4.0~V \leq V_{DD} \leq 5.5~V$	44		110		ns
Note 1		$2.7~V \leq V_{DD} \leq 5.5~V$	44		110		ns
SIp hold time (from SCKp↑) Note 2	tksi1		19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note 4}		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.
- **5.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

2. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00))



(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +105^{\circ}C^{\text{Note } 6}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Condit	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		
				MIN.	MAX.	MIN.	MAX.		
SCKp cycle time	tkcy2	$4.0~V \le V_{DD} \le 5.5~V$	20 MHz < f _{MCK}	8/fмск		-		ns	
Note 5			fмcк ≤ 20 MHz	6/ƒмск		6/ƒмск		ns	
		$2.7~V \le V_{DD} \le 5.5~V$	16 MHz < fмск	8/fмск		_		ns	
			fмcк ≤ 16 MHz	6/fмск		6/ƒмск		ns	
SCKp high-/low-level width	t _{KH2} ,			tксу2/2		tkcy2/2		ns	
SIp setup time (to SCKp↑) ^{Note 1}	tsık2			1/fмск+20		1/fмск+30		ns	
Slp hold time (from SCKp↑) ^{Note 2}	tksı2			1/fмск+31		1/fмск+31		ns	
Delay time from SCKp↓ to SOp outputNote 3	tkso2	C = 30 pF ^{Note 4}			2/fмск+ 44		2/fмск+ 110	ns	

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - **6.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

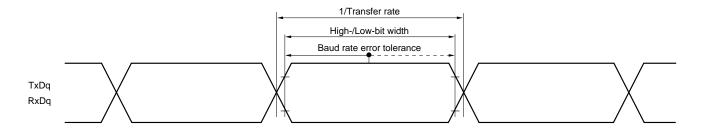
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

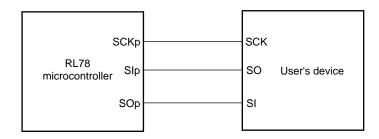
2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

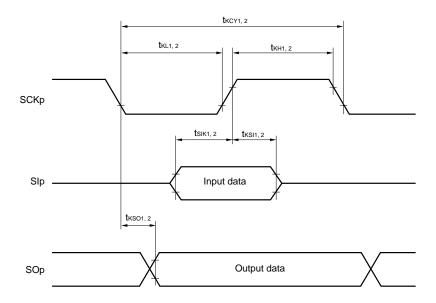
n: Channel number (mn = 00))



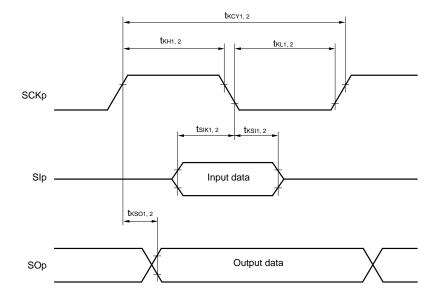
Simplified SPI (CSI) mode connection diagram (during communication at same potential)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00)

2. m: Unit number, n: Channel number (mn = 00)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions			HS (high-speed main) Mode		peed main) ode	Unit
						MAX.	MIN.	MAX.	
Transfer		Reception	4.0 V	$V \le V_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le V_{b} \le 4.0 \text{ V}$		fmck/6 ^{Note 1}		fmck/6 ^{Note 1}	bps
rate				Theoretical value of the maximum transfer rate fmck = fclk Note 2		5.3		1.3	Mbps
			2.7 V	$1 \le V_{DD} \le 4.0 \text{ V}, 2.3 \text{ V} \le V_{b} \le 2.7 \text{ V}$		fmck/6 ^{Note 1}		fmck/6 ^{Note 1}	bps
				Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 2}		5.3		1.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz ($2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$)

LS (low-speed main) mode: $8 \text{ MHz} (2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}), \text{ T}_{A} = -40 \text{ to } +85^{\circ}\text{C}.$

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note } 5}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions			gh-speed) Mode	LS (low-speed main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	4.0 V	$\leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V$		Note 1		Note 1	bps
				Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.8 ^{Note 2}		2.8 ^{Note 2}	Mbps
			2.7 V	$\leq V_{DD} \leq 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V$		Note 3		Note 3	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 k Ω , V_b = 2.3 V		1.2 ^{Note 4}		1.2 ^{Note 4}	Mbps

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when $4.0~V \le V_{DD} \le 5.5~V$ and $2.7~V \le V_{b} \le 4.0~V$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{2.2}{V_b})\} \times 3} [bps]$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq V_{DD} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \ [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- **5.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to $+85^{\circ}$ C.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

 $\textbf{Remarks 1.} \quad \mathsf{Rb}[\Omega] \text{: } \mathsf{Communication line (TxDq) pull-up resistance,}$

 $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage

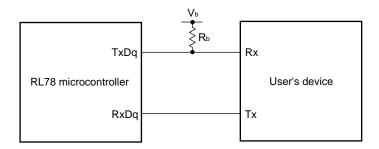
- 2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

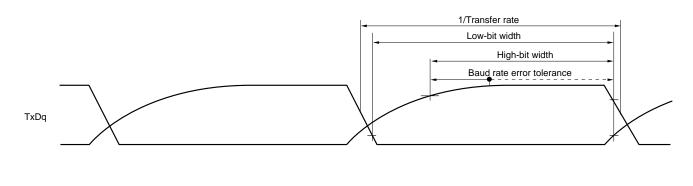
m: Unit number, n: Channel number (mn = 00 to 03))

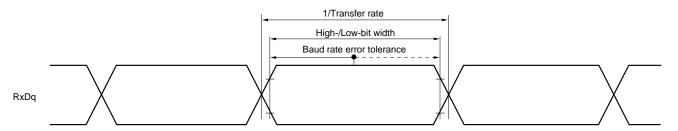


UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $V_b[V]$: Communication line voltage

2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

(5) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note } 3}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high main) N	•	LS (low-s	•	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcY1 ≥ 2/fcLK	$\begin{split} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{split}$	200		1150		ns
			$ 2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, $ $ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 2.7 \text{ k}\Omega $	300		1150		ns
SCKp high-level width	t кн1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	tkcy1/2 - 50		tkcy1/2 - 75		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le \text{C}_{b} = 30 \text{ pF}, \text{ F}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	tксу1/2 — 120		tксү1/2 – 170		ns
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	tксу1/2 — 7		tkcy1/2 - 50		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	tксү1/2 — 10		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸ1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	81		479		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	177		479		ns
SIp hold time (from SCKp↑)	t _{KSI1}		$5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	10		19		ns
Note 1		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $6.8b = 2.7 \text{ k}\Omega$	10		19		ns
Delay time from SCKp↓ to SOp	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$		60		100	ns
output ^{Note 1}		$2.7 \text{ V} \le \text{V}_{DD} \le \text{C}_{b} = 30 \text{ pF}, \text{ F}$			130		195	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸ1	$4.0 \text{ V} \leq \text{V}_{DD} \leq$ $C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	44		110		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le \text{C}_{b} = 30 \text{ pF}, \text{ F}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	44		110		ns
SIp hold time (from SCKp↓)	t _{KSI1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le V_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	10		19		ns
Note 2		$2.7 \text{ V} \le \text{V}_{DD} \le \text{C}_{b} = 30 \text{ pF}, \text{ F}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	10		19		ns
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \leq \text{V}_{DD} \leq$ $C_b = 30 \text{ pF, F}$	$5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $R_b = 1.4~k\Omega$		10		25	ns
SOp outputNote 2		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$6.4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$		10		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

- 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- **Remarks 1.** $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

(6) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(Ta = -40 to +105°C Note 3, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	HS (high-speed	d main) Mode	LS (low-speed	d main) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$\begin{split} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{split}$	300		1150		ns
			$\begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	500		1150		ns
SCKp high-level width	t кн1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, I}$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $\text{R}_{\text{b}} = 1.4 \text{ k}\Omega$	tkcy1/2 - 75		tксү1/2 – 75		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \cdot \text{C}_{b} = 30 \text{ pF, I}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $\text{R}_{\text{b}} = 2.7 \text{ k}\Omega$	tксү1/2 – 170		tксү1/2 — 170		ns
SCKp low-level width	t _{KL1}	4.0 V ≤ V _{DD} ≤ C _b = 30 pF, I	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $\text{R}_{\text{b}} = 1.4 \text{ k}\Omega$	tkcy1/2 - 12		tксү1/2 – 50		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \cdot \text{C}_{b} = 30 \text{ pF}, \text{ I}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $R_{\text{b}} = 2.7 \text{ k}\Omega$	tксу1/2 – 18		tксү1/2 – 50		ns
SIp setup time (to SCKp↑)	tsıĸı	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ I}$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $\text{R}_{\text{b}} = 1.4 \text{ k}\Omega$	81		479		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq C_b = 30 \text{ pF, I}$	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $R_{\text{b}} = 2.7 \text{ k}\Omega$	177		479		ns
SIp hold time (from SCKp↑)	t _{KSI1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, I$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $\text{R}_{\text{b}} = 1.4 \text{ k}\Omega$	19		19		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \cdot \text{C}_{b} = 30 \text{ pF, I}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 k Ω	19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, I}$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $\text{R}_{\text{b}} = 1.4 \text{ k}\Omega$		100		100	ns
oop output		$2.7 \text{ V} \leq \text{V}_{DD} \cdot \text{C}_{b} = 30 \text{ pF, I}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 k Ω		195		195	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸı	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, I}$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ R_{b} = 1.4 k Ω	44		110		ns
		$2.7 \text{ V} \le \text{V}_{DD} + \text{C}_{b} = 30 \text{ pF}, \text{ I}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 k Ω	44		110		ns
SIp hold time (from SCKp↓)	t _{KSI1}	$4.0 \text{ V} \le \text{V}_{DD} \le \text{Cb} = 30 \text{ pF},$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ Rb = 1.4 k Ω	19		19		ns
			$<$ 4.0 V, 2.3 V \le V _b \le 2.7 V, Rb = 2.7 kΩ	19		19		ns
Delay time from SCKp↑ to SOp outputNote 2	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le \text{Cb} = 30 \text{ pF},$	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ Rb = 1.4 k Ω		25		25	ns
COp Gatput			$<$ 4.0 V, 2.3 V \le V _b \le 2.7 V, Rb = 2.7 kΩ		25		25	ns

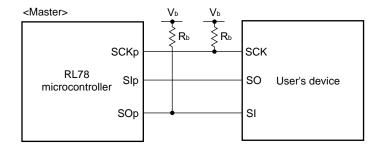
Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

(Caution and Remarks are listed on the next page.)

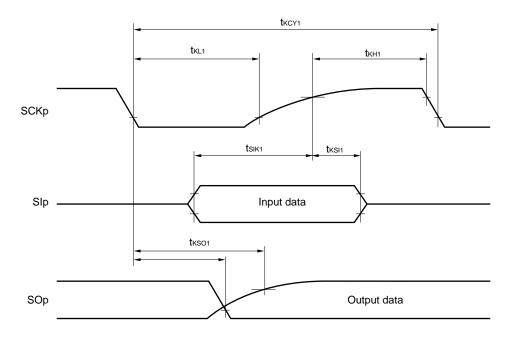
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

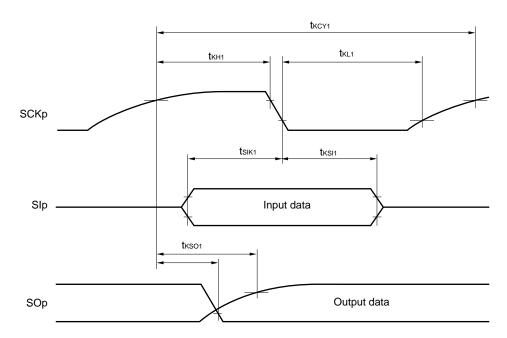


- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

(7) DALI/UART4 mode

(T_A = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		peed main) ode	LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Transfer rate				fмск/12		fмск/12	bps
		Maximum transfer rate theoretical value HS: fclk = 32 MHz, fmck = fclk LS: fclk = 8 MHz, fmck = fclk		2.6		0.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register mn (SPS4).)

Caution Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

2.5.2 Serial interface IICA

(1) I²C standard mode

(T_A = -40 to +105°C Note 3, 2.7 V \leq V_{DD} \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (hig main)		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode: fcLK≥ 1 MHz	0	100	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		4.7		μS
Hold time ^{Note 1}	thd:sta		4.0		4.0		μS
Hold time when SCLA0 = "L"	tLOW		4.7		4.7		μS
Hold time when SCLA0 = "H"	tніgн		4.0		4.0		μS
Data setup time (reception)	tsu:dat		250		250		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	3.45	μS
Setup time of stop condition	tsu:sto		4.0		4.0		μS
Bus-free time	t BUF		4.7		4.7		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- 2. The maximum value (MAX.) of thd:dat is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

RENESAS

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$

<R>

(2) I²C fast mode

(Ta = -40 to +105°C $^{\text{Note 3}}$, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	fast mode: fcLκ≥ 3.5 MHz	0	400	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		0.6		μS
Hold time ^{Note 1}	thd:sta		0.6		0.6		μS
Hold time when SCLA0 = "L"	tLOW		1.3		1.3		μS
Hold time when SCLA0 = "H"	tніgн		0.6		0.6		μS
Data setup time (reception)	tsu:dat		100		100		ns
Data hold time (transmission)Note 2	thd:dat		0	0.9	0	0.9	μS
Setup time of stop condition	tsu:sto		0.6		0.6		μS
Bus-free time	t BUF		1.3		1.3		μS

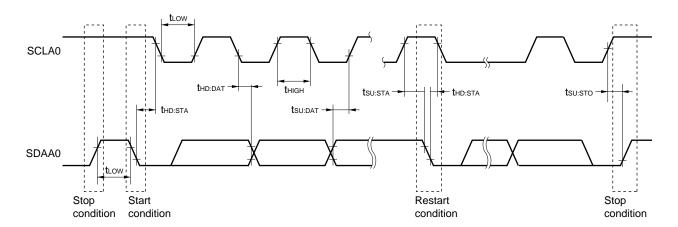
Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

	Reference Voltage						
Input channel	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}				
ANI0 to ANI2, ANI4 to ANI7	See 2.6.1 (1).	See 2.6.1 (3) .	See 2.6.1 (4).				
ANI16 to ANI19	See 2.6.1 (2).						
Internal reference voltage Temperature sensor output voltage	See 2.6.1 (1).		_				

(1) When reference voltage (+)= AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	IS	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2, ANI4 to ANI7	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	3.1875		39	μS
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	3.5625		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±1.5	LSB
Analog input voltage	VAIN	ANI2, ANI4 to ANI7		0		AVREFP	V
		Internal reference voltage (HS (high-speed main) mode)		V _{BGR} Note 4		V
		Temperature sensor output v (HS (high-speed main) mode	· ·	\	/ _{TMPS25} Note	4	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. See 2.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI19

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{\text{REFP}}, \text{Reference voltage (-)} = \text{AV}_{\text{REFM}} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}			1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target ANI pin : ANI16 to ANI19	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±0.35	%FSR
Integral linearity error ^{Note}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AVREFP and VDD	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

(T_A = -40 to +105°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (-) = V_{SS})

Parameter	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	3.1875		39	μS
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	3.5625		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution				±0.60	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution				±4.0	LSB
Differential linearity errorNote 1	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI2, ANI4 to ANI7	•	0		V_{DD}	V
		ANI16 to ANI19		0		V _{DD}	V
		Internal reference voltage (HS (high-speed main) mode	e)		V _{BGR} Note 3		V
		Temperature sensor output (HS (high-speed main) mode	o .	\	/TMPS25 ^{Note :}	3	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. See 2.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

(T_A = -40 to +105°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR}Note 3, Reference voltage (-) = AV_{REFM} = 0 V^{Note 4}, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv	8-bit resolution	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution			±2.0	LSB
Differential linearity errorNote 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		V _{BGR} Note 3	V

- **Notes 1.** Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. See 2.6.2 Temperature sensor/internal reference voltage characteristics.
 - **4.** When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AVREFM.

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AVREFM.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

2.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	V _{BGRT}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvтмps	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	tamp		5			μS

2.6.3 Programmable gain amplifier

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le AV_{REFP} = V_{DD} \le 5.5 \text{ V}, V_{SS} = AV_{REFM} = 0 \text{ V})$

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9V _{DD} /	V
							gain	
Gain error ^{Note 1}		4, 8 tim	es				±1	%
		16 time	S				±1.5	%
		32 time	s			±2	%	
Slew rate ^{Note 1}		Rising edge	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	4, 8 times	4			V/μs
				16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$	4, 8 times	1.8			V/μs
				16, 32 times	0.5			V/μs
	SR _{FPGA}	Falling	$4.0~V \leq V_{DD} \leq 5.5~V$	4, 8 times	3.2			V/μs
		edge		16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$	4, 8 times	1.2			V/μs
				16, 32 times	0.5			V/μs
Operation stabilization wait timeNote 2	t PGA	4, 8 times		5			μS	
		16, 32 t	16, 32 times					μS

Notes 1. When V_{IPGA} = 0.1V_{DD}/gain to 0.9V_{DD}/gain.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.

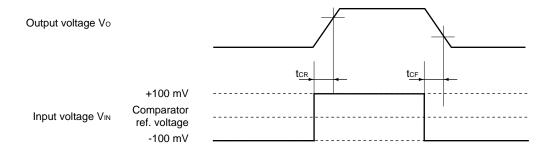
2.6.4 Comparator

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le AV_{REFP} = V_{DD} \le 5.5 \text{ V}, V_{SS} = AV_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		V _{DD}	V
		СМРСОМ	0.045		0.9V _{DD}	V
Internal reference voltage deviation	△VIREF	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcf	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait timeNote 1	tcmp	$3.3~V \leq V_{DD} \leq 5.5~V$	1			μs
		2.7 V ≤ V _{DD} < 3.3 V	3			μs
Reference voltage stabilization wait time	tvr	CVRE: 0 to 1 ^{Note 2}	10			μS

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - 2. Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.

Remark These characteristics apply when AVREFP is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AVREFM is selected as GND of the internal reference voltage by using the CVRVS1 bit.

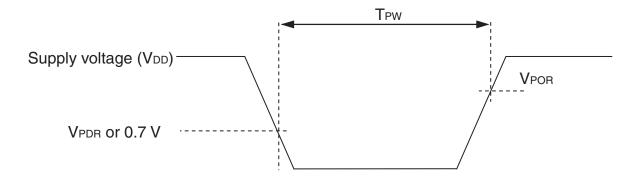


2.6.5 POR circuit characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	Power supply rise time	1.45	1.51	1.57	V
	V _{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width ^{Note}	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _{LVD0}	Power supply rise time	3.97	4.06	4.14	٧
voltage			Power supply fall time	3.89	3.98	4.06	٧
		V _{LVD1}	Power supply rise time	3.67	3.75	3.82	V
			Power supply fall time	3.59	3.67	3.74	V
		V _{LVD2}	Power supply rise time	3.06	3.13	3.19	V
		Power supply fall time	2.99	3.06	3.12	V	
		V _{LVD3}	Power supply rise time	2.95	3.02	3.08	V
			Power supply fall time	2.89	2.96	3.02	V
		V _{LVD4}	Power supply rise time	2.85	2.92	2.97	V
			Power supply fall time	2.79	2.86	2.91	V
		V _{LVD5}	Power supply rise time	2.75	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
Minimum pul	se width	tuw		300			μS
Detection de	lay time					300	μs

LVD Detection Voltage of Interrupt & Reset Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _{LVD0}	V _{POC2} ,	V _{POC2} , V _{POC1} , V _{POC0} = 0, 1, 1, falling reset voltage: 2.7 V			2.75	2.81	V
mode VLVD1 VLVD2 VLVD3		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.85	2.92	2.97	V	
				Falling interrupt voltage	2.79	2.86	2.91	V
	V _{LVD2}	V _{LVD2}	, ,	Rising release reset voltage	2.95	3.02	3.08	V
				Falling interrupt voltage	2.89	2.96	3.02	V
	V _{LVD3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.97	4.06	4.14	V
				Falling interrupt voltage	3.89	3.98	4.06	V

2.6.7 Supply voltage rise inclination characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SV _{DD}				54	V/ms

Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 32.4 AC Characteristics.

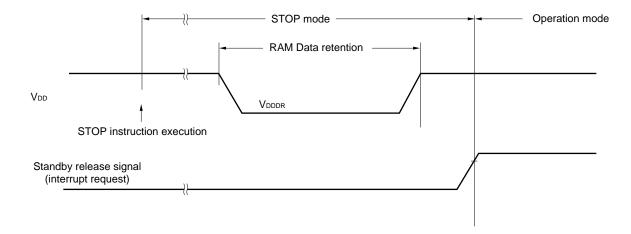
2.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltageNote 2	VDDDR		1.44 ^{Note 1}		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.

Caution When CPU is operated at the voltage of out of the operation voltage range, RAM data is not retained. Therefore, set STOP mode before the supplied voltage is below the operation voltage range.



2.8 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	1		32	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years, T _A = 85°C ^{Note 3}	1,000			Times
Number of data flash		Retained for 1 year, T _A = 25°C ^{Note 3}		1,000,000		
rewrites ^{Notes 1, 2, 3}		Retained for 5 years, T _A = 85°C ^{Note 3}	100,000			
		Retained for 20 years, T _A = 85°C ^{Note 3}	10,000			

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer and Renesas Electronics self programming library
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

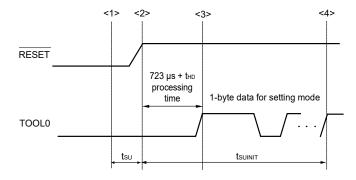
(T_A = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps

2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tно	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Complete the baud rate setting by UART reception.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.

 t_{SU} : How long from when the TOOL0 pin is placed at the low level until an external reset ends

thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

3. ELECTRICAL SPECIFICATIONS

(M: Industrial applications, $T_A = -40$ to +125°C)

In this chapter, shows the electrical specifications of the target products.

Target products (M: Industrial applications): $T_A = -40 \text{ to } +125^{\circ}\text{C}$ R5F107xxMxx

- Cautions 1. The RL78/I1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 Functions for each product in the RL78/I1A User's Manual.
 - 3. When any of these products are used at 105° C or lower, see 2. ELECTRICAL SPECIFICATIONS (T_A = -40 to $+105^{\circ}$ C).



3.1 Absolute Maximum Ratings

Absolute Maximum Ratings $(T_A = 25^{\circ}C)$ (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VII	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	−0.3 to V _{DD} +0.3 ^{Note 2}	٧
Output voltage	Vo1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	Val1	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** AV_{REF (+)}: + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage

Absolute Maximum Ratings (T_A = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40	mA
		Total of all pins –170 mA	P02, P03, P40, P120	–70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	Іон2	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins 170 mA	P02, P03, P40, P120	70	mA
			P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	lol2	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operation	on mode	-40 to +125	°C
temperature		In flash memory p	programming mode	-40 to +105	
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock frequency (fx) ^{Note}	Ceramic resonator/ crystal resonator		1.0		20.0	MHz
XT1 clock frequency (f _{XT}) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. See **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, see 5.4 System Clock Oscillator in the RL78/I1A User's Manual.

3.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Note 1}	fін		1		32	MHz
High-speed on-chip oscillator		T _A = -20 to 85°C	-1		+1	%
clock frequency accuracyNote 2		T _A = -40 to 105°C	-1.5		+1.5	%
		T _A = -40 to 125°C When 16 MHz selected	-2		+2	%
Low-speed on-chip oscillator clock frequency	fıL			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - 2. This indicates the oscillator characteristics only. See AC Characteristics for instruction execution time.

Remark When using the device at an ambient temperature that exceeds T_A = 105°C, the selectable oscillation frequency is 16 MHz max.

3.2.3 PLL characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	fpllin	High-speed system clock is selected (f _{MX} = 4 MHz)	3.92	4.00	4.08	MHz
frequency ^{Note}		High-speed on-chip oscillator clock is selected (f _{IH} = 4 MHz)	3.92	4.00	4.08	MHz
PLL output clock frequency ^{Note}	fpll			fpllin × 16		MHz

Note This only indicates the oscillator characteristics. See AC Characteristics for instruction execution time.

Remark When using the device at an ambient temperature that exceeds $T_A = 105$ °C, only 16 MHz (f_{PLL} × 1/4) can be selected as the CPU operating frequency.



3.3 DC Characteristics

3.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	І он1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~V \leq V_{DD} \leq 5.5~V$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-1.0	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			-9.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-3.0	mA
		Total of P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206 (When duty $\leq 70\%^{\text{Note 3}}$)	$4.0~V \leq V_{DD} \leq 5.5~V$			-21.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-6.0	mA
		Total of all pins	$4.0~V \leq V_{DD} \leq 5.5~V$			-21.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-9.0	mA
	І он2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$			-0.4	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	l _{OL1}	Per pin for P02, P03, P05, P06,	$4.0~V \leq V_{DD} \leq 5.5~V$			8.5 ^{Note 2}	mA
IOW ^{Note 1}		P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			1.5 ^{Note 2}	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{DD} \leq 5.5~V$			20.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			5.0	mA
		D75 to D77 D147 D200 to D206	$4.0~V \leq V_{DD} \leq 5.5~V$			20.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			10.0	mA
		Total of all pins	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
		(When duty ≤ 70% ^{Note 3})	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			15.0	mA
lo _{L2}	l _{OL2}	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{DD} \leq 5.5~V$			0.4 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$			1.6	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoL × 0.7)/(n × 0.01)
- <Example> Where n = 80% and IoL = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0.8V _{DD}		V _{DD}	>
	V _{IH2}	P03, P10, P11	TTL input buffer $4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	2.1		V _{DD}	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	2.0		V _{DD}	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	1.5		V _{DD}	V
Input voltage, low	VIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	>
	V _{IL2}	P03, P10, P11	TTL input buffer $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0		0.8	V
			TTL input buffer 3.3 V ≤ V _{DD} < 4.0 V	0		0.5	V
			TTL input buffer $2.7 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V}$	0		0.32	V

Caution The maximum value of VIH of pins P02, P10 to P12 is VDD, even in the N-ch open-drain mode.

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OH1}} = -3.0 \text{ mA}$	V _{DD} - 0.7			V
		P200 to P206	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -1.0 \text{ mA}$	V _{DD} - 0.5			V
Voh	V _{OH2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \ \mu\text{A}$	V _{DD} - 0.5			V
Output voltage,	V _{OL1}		$4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 8.5 \text{ mA}$			0.7	V
		P200 to P206	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 4.0 \text{ mA}$			0.4	V
		$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OL1}} = 1.5 \text{ mA}$			0.4	V	
	V _{OL2}	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL2} = 400 \ \mu\text{A}$			0.4	V

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol	Condition	ıs		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	V _I = V _{DD}				1	μA
	ILIH2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V _I = V _{DD}	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
Input leakage current, low	ILIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	<u> </u>				-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μA
				In resonator connection			-10	μΑ
On-chip pull-up resistance	Ru	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	V _I = Vss, In input port		10	20	100	kΩ

3.3.2 Supply current characteristics

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V) (1/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit						
Supply	I _{DD1}	Operating	HS (high-	f _{IH} = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.8	mA						
Current Note 1		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		2.9	4.8	mA						
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	5.6	mA						
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	Resonator connection		3.3	5.7	mA						
			mode	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	5.6	mA						
				V _{DD} = 3.0 V	Resonator connection		3.3	5.7	mA						
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	3.3	mA						
				V _{DD} = 5.0 V	Resonator connection		2.0	3.3	mA						
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	3.3	mA						
			ı		V _{DD} = 3.0 V	Resonator connection		2.0	3.3	mA					
									HS (high-	f _{IH} = 4 MHz Note 3	V _{DD} = 5.0 V		3.3	6.5	mA
			speed main) mode ^{Note 5}	fPLL = 64 MHz, fcLK = 16 MHz	V _{DD} = 3.0 V		3.3	6.5	mA						
			Subsystem	f _{SUB} = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μA						
			clock operation	T _A = -40°C	Resonator connection		4.4	6.2	μA						
			operation	f _{SUB} = 32.768 kHz ^{Note 4} T _A = +25°C	Square wave input		4.2	6.0	μA						
					Resonator connection		4.4	6.2	μA						
				f _{SUB} = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μA						
				T _A = +50°C	Resonator connection		4.5	7.4	μA						
				f _{SUB} = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μA						
				T _A = +70°C	Resonator connection		4.6	8.3	μA						
				fsub = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μA						
				T _A = +85°C	Resonator connection		5.4	11.6	μA						
				fsuB = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μА						
				T _A = +105°C	Resonator connection		7.1	21.0	μА						
				1	Square wave input		11.1	51.2	μA						
					T _A = +125°C	Resonator connection		11.3	51.4	μА					

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main) modes.
 - •The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.
 - In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1}$ MHz to 20 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2} Note 2	HALT	HS (high-	f _{IH} = 16 MHz Note 4	V _{DD} = 5.0 V		0.50	2.0	mA
current Note 1		mode	speed main) mode ^{Note 6}		V _{DD} = 3.0 V		0.50	2.0	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	2.2	mA
			speed main)	V _{DD} = 5.0 V	Resonator connection		0.50	2.3	mA
			mode ^{Note 6}	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	2.2	mA
				V _{DD} = 3.0 V	Resonator connection		0.50	2.3	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.22	mA
				V _{DD} = 5.0 V	Resonator connection		0.30	1.28	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.22	mA
				V _{DD} = 3.0 V	Resonator connection		0.30	1.28	mA
			HS (high-	f _H = 4 MHz ^{Note 4}	V _{DD} = 5.0 V		0.95	3.7	mA
		mode ^{Note 6}	fPLL = 64 MHz, fcLK = 16 MHz	V _{DD} = 3.0 V		0.95	3.7	mA	
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.70	μΑ
			clock	T _A = -40°C	Resonator connection		0.47	0.89	μA
			operation	fsuB = 32.768 kHz ^{Note 5}	Square wave input		0.33	0.70	μΑ
				T _A = +25°C	Resonator connection		0.52	0.89	μA
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	1.90	μΑ
					Resonator connection		0.60	2.09	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.54	2.80	μΑ
					Resonator connection		0.73	2.99	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.27	6.10	μΑ
				T _A = +85°C	Resonator connection		1.46	6.29	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		3.04	15.5	μΑ
				T _A = +105°C	Resonator connection		3.23	15.7	μΑ
				f _{SUB} = 32.768 kHz ^{Note 5}	Square wave input		7.20	45.2	μΑ
				T _A = +125°C	Resonator connection		7.53	45.5	μΑ
	IDD3	STOP	T _A = -40°C				0.18	0.50	μА
		mode	T _A = +25°C				0.23	0.50	μΑ
		Note 7	T _A = +50°C				0.27	1.70	μΑ
			T _A = +70°C	$T_A = +70$ °C $T_A = +85$ °C			0.44	2.60	μΑ
			T _A = +85°C				1.17	5.90	μΑ
			T _A = +105°C				2.94	15.3	μΑ
			•						

(Notes and Remarks are listed on the next page.)

 $T_A = +125$ °C





7.14 45.1 μA



- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or Vss. The following points apply in the HS (high-speed main) modes.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.

In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- 4. When high-speed system clock and subsystem clock are stopped.
- **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$ to 20 MHz
- 7. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	FIL Note 1						0.20		μΑ
RTC operating current	IRTC Notes 1, 2, 3						0.02		μА
12-bit interval timer operating current	 IT Notes 1, 2, 4						0.02		μА
Watchdog timer operating current	WDT Notes 1, 2, 5	fı∟ = 15 kHz					0.22		μА
A/D converter operating current	IADC Notes 1, 6	When conversion maximum spee		Normal mode,	AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
A/D converter reference voltage current	ADREF Note 1						75.0		μА
Temperature sensor operating current	I _{TMPS} Note 1						75.0		μА
LVD operating current	LVDNotes 1, 7						0.08		μА
Self-programming operating current	IFSP Notes 1, 8						2.5	12.2	mA
Programmable	I _{PGA} Note 9				AV _{REFP} = V _{DD} = 5.0 V		0.21	0.37	mA
gain amplifier operating current					AV _{REFP} = V _{DD} = 3.0 V		0.18	0.35	mA
Comparator	I _{CMP} Note 10	When one com	parato	r channel is	AV _{REFP} = V _{DD} = 5.0 V		41.4	74	μА
operating current		operating			AV _{REFP} = V _{DD} = 3.0 V		37.2	71	μА
	IVREF	When one inter	nal ref	erence voltage	AV _{REFP} = V _{DD} = 5.0 V		14.8	31	μА
		circuit is operat	ing		AV _{REFP} = V _{DD} = 3.0 V		8.9	24	μА
Programmable	IREF Note 11				AV _{REFP} = V _{DD} = 5.0 V		3.2	6.1	μА
gain amplifier/ comparator reference current source					AV _{REFP} = V _{DD} = 3.0 V		2.9	4.9	μΑ
BGO operating current	BGO ^{Note 12}						2.50	12.2	mA
SNOOZE	I _{SNOZ} Note 1	A/D converter	The	mode is perform	ed ^{Note 13}		0.50	1.10	mA
operating current		operation		A/D conversion on all mode, AVREF	operations are performed, $P = V_{DD} = 5.0 \text{ V}$		1.20	2.17	mA
		Simplified SPI (ified SPI (CSI)/UART operation				0.70	1.27	mA

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Current flowing to the VDD.
 - 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
 - 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock is operating in operating mode or in HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
 - 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and fill operating current). The current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
 - 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IWDT, when the watchdog timer is operating.
 - **6.** Current flowing only to the A/D converter. The supply current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC}, when the A/D converter is operating in operating mode or in HALT mode.
 - **7.** Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of ldd, ldd or ldd and llvd when the LVD circuit is in operation.
 - **8.** Current flowing during self-programming operation.
 - **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
 - **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
 - **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
 - **12.** Current flowing only during data flash rewrite.
 - 13. See 21.3.3 SNOOZE mode in the RL78/I1A User's Manual for shift time to the SNOOZE mode.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - 4. Temperature condition of the TYP. value is TA = 25°C
 - 5. Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AVREFP = VDD = 5.0 V)

```
ICMP × 3 + IVREF + IPGA + IREF 
= 41.4 [\mu A] × 3 + 14.8 [\mu A] × 1 + 210 [\mu A] + 3.2 [\mu A] 
= 352.2 [\mu A]
```

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AVREFP = VDD = 5.0 V)

```
ICMP × 2 + IIREF
= 41.4 [\mu A] × 2 + 3.2 [\mu A]
= 86.0 [\mu A]
```



3.4 AC Characteristics

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

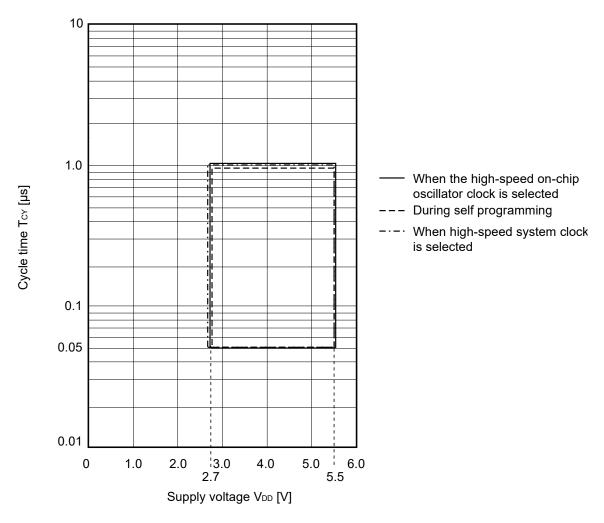
Items	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Тсч	Main system clock (f _{MAIN}) operation HS (high-speed main) mode		0.05		1	μs
		Subsystem clock (fsub)	operation	28.5	30.5	31.3	μS
		In the self programming main) mode	•	0.05		1	μs
External system clock frequency	fex	,	•	1.0		20.0	MHz
	fexs			32		35	kHz
External system clock input high-	texh, texl			24			ns
level width, low-level width	texhs, texhs		13.7			μS	
TI03, TI05, TI06, TI07 input high- level width, low-level width	tтін, tті∟			2/fмск+10			ns
TO03, TO05, TO06, TKBO00,	f то	HS (high-speed main)	$4.0~V \leq V_{DD} \leq 5.5~V$			5	MHz
TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to TKCO05 output frequency (When duty = 50%)		mode	2.7 V ≤ V _{DD} < 4.0 V			4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0, INTP3, INTP4, INTP9 to INTP11, INTP20 to INTP23	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	1			μs
RESET low-level width	trsl			10			μS

Remark fmck: Timer array unit operation clock frequency

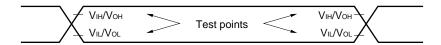
(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation

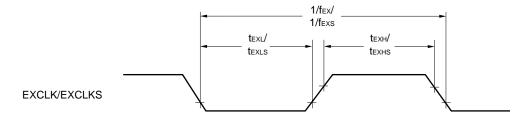
Tcy vs VDD (HS (high-speed main) mode)



AC Timing Test Points

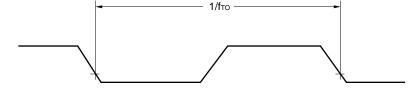


External System Clock Timing



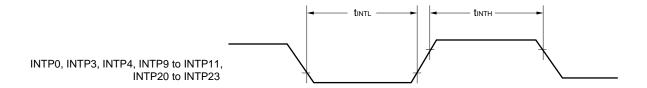
TI/TO Timing



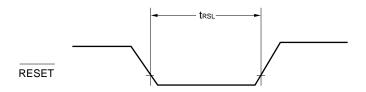


T003, T005, T006, TKB000, TKB001, TKB010, TKB011, TKB020, TKB021, TKC000 to TKC005

Interrupt Request Input Timing

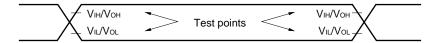


RESET Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

(1) During communication at same potential (UART mode)

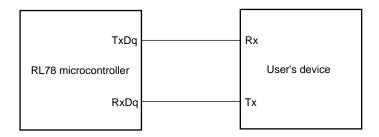
 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate ^{Note 1}					fмск/6	bps
		tra	neoretical value of the maximum ansfer rate _{CK} = f _{CLK} ^{Note 2}		3.3	Mbps

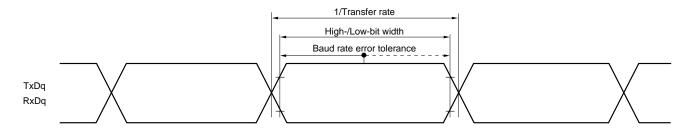
- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 20 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03))

<R>

(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		` `	HS (high-speed main) Mode	
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$4.0~V \leq V_{DD} \leq 5.5~V$	250		ns
			$2.7~V \leq V_{DD} \leq 5.5~V$	500		ns
SCKp high-/low-level width	t кн1,	$4.0~V \leq V_{DD} \leq 5.5$	$4.0~V \leq V_{DD} \leq 5.5~V$			ns
	t _{KL1}	$2.7~V \leq V_{DD} \leq 5.5$	V	tkcy1/2 - 40		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸ1	$4.0~V \leq V_{DD} \leq 5.5$	V	80		ns
		$2.7~V \leq V_{DD} \leq 5.5$	V	80		ns
SIp hold time (from SCKp↑)Note 2	t _{KSI1}			40		ns
Delay time from SCKp↓ to SOp outputNote 3	t _{KSO1}	C = 30 pF ^{Note 4}			80	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

2. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00))

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(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

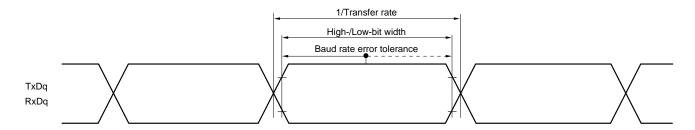
Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time ^{Note 5}	tkcy2	$4.0~V \leq V_{DD} \leq 5.5~V$	fмcк ≤ 20 MHz	6/fмск		ns
		$2.7~V \leq V_{DD} \leq 5.5~V$	16 MHz < fмск	8/fмск		ns
			fмcк ≤ 16 MHz	6/fмск		ns
SCKp high-/low-level width	tкн2, tкL2			tксү2/2		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıк2			1/fмск+40		ns
SIp hold time (from SCKp↑)Note 2	tksı2			1/fмск+60		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso2	C = 30 pF ^{Note 4}			2/fмск+80	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

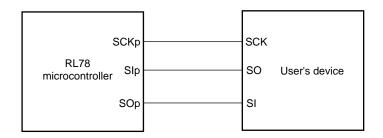
2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00))



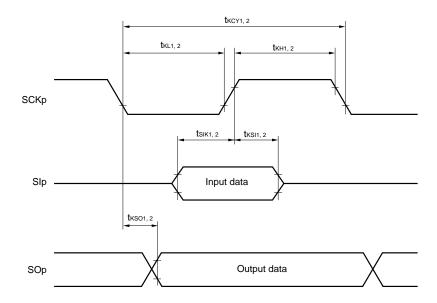


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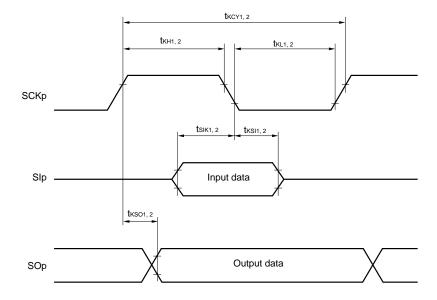
Simplified SPI (CSI) mode connection diagram (during communication at same potential)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00)

2. m: Unit number, n: Channel number (mn = 00)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions			HS (high-speed main) Mode	
					MIN.	MAX.	
Transfer rate		Reception	$\begin{array}{c} 4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V} \end{array}$			fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps
			$ 2.7 \ V \le V_{DD} < 4.0 \ V, \\ 2.3 \ V \le V_b \le 2.7 \ V $			fmck/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps

- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 20 MHz ($2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03)

(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions			HS (high-speed main) Mode	
					MIN.	MAX.	
Transfer rate		Transmission	$4.0~V \leq V_{DD} \leq 5.5~V,$			Note 1	bps
			$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 k Ω , V_b = 2.7 V		2.8 ^{Note 2}	Mbps
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V},$			Note 3	bps
			$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 ^{Note 4}	Mbps

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{2.2}{V_b})\} \times 3} [bps]$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

$$\label{eq:maximum transfer rate} \begin{aligned} & \frac{1}{\{-C_b \times R_b \times \ln{(1-\frac{2.0}{V_b})}\} \times 3} \end{aligned} \text{ [bps]}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

 $\mbox{\bf Remarks 1.} \quad \mbox{\bf R}_b[\Omega] \mbox{: Communication line (TxDq) pull-up resistance,} \\$

Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

- 2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency

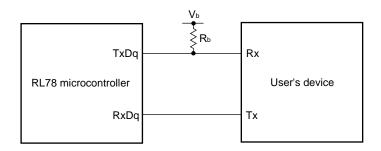
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03))

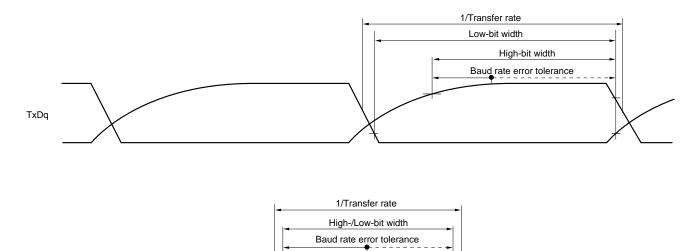


RxDq

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (Vpb tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $V_b[V]$: Communication line voltage

2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

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(5) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	HS (high-sp Mod	,	Unit ns ns ns ns ns ns ns
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ \begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	600		ns
				1000		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $R_b = 1.4~k\Omega$	tkcy1/2 - 80		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq V _b \leq 2.7 V, $R_b = 2.7 \ k\Omega$	tксү1/2 — 170		ns
SCKp low-level width t _{KL1}		$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_{\textrm{b}} \leq 4.0~\textrm{V},$ $R_{\textrm{b}} = 1.4~\textrm{k}\Omega$	tkcy1/2 - 28		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$\begin{array}{l} <4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ R_{\text{b}} = 2.7 \text{ k}\Omega \end{array}$	tkcy1/2 - 40		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$6.5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_{\textrm{b}} \leq 4.0~\textrm{V},$ $R_{\textrm{b}} = 1.4~\textrm{k}\Omega$	160		ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$\begin{array}{l} 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ R_{\text{b}} = 2.7 \text{ k}\Omega \end{array}$	250		ns ns ns
SIp hold time t _{KSI1} (from SCKp↑) ^{Note 1}		$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	40		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq \text{C}_{b} = 30 \text{ pF, F}$	$\begin{array}{l} <4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ R_{\text{b}} = 2.7 \text{ k}\Omega \end{array}$	40		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_{\textrm{b}} \leq 4.0~\textrm{V},$ $R_{\textrm{b}} = 1.4~\textrm{k}\Omega$		160	ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq V _b \leq 2.7 V, $R_b = 2.7 \ k\Omega$		250	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸı	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $R_b = 1.4~k\Omega$	80		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq C_b = 30 \text{ pF}, \text{ F}$	$\begin{array}{l} <4.0 \text{ V}, \ 2.3 \text{ V} \leq V_b \leq 2.7 \text{ V}, \\ R_b = 2.7 \text{ k}\Omega \end{array}$	80		ns
SIp hold time (from SCKp↓) ^{Note 2}	t _{KSI1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_{\textrm{b}} \leq 4.0~\textrm{V},$ $R_{\textrm{b}} = 1.4~\textrm{k}\Omega$	40		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k Ω	40		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$6.5.5~\textrm{V},~2.7~\textrm{V} \leq \textrm{V}_{\textrm{b}} \leq 4.0~\textrm{V},$ $R_{\textrm{b}} = 1.4~\textrm{k}\Omega$		80	ns
		2.7 V ≤ V _{DD} < C _b = 30 pF, F	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$		80	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

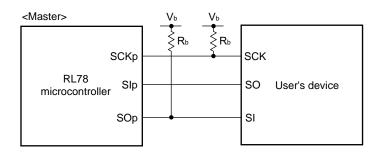
(Caution and Remarks are listed on the next page.)

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Caution

Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)



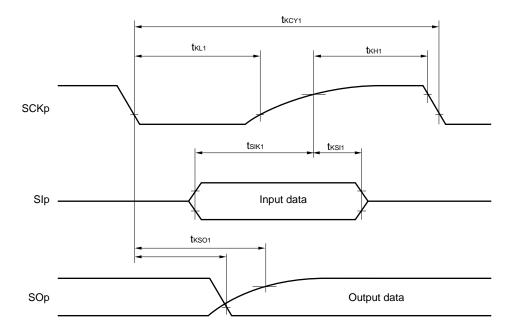
- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)



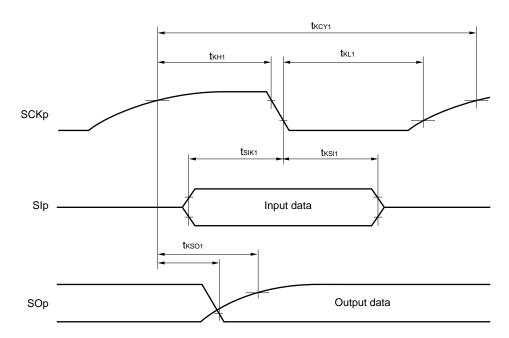
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Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)

(6) DALI/UART4 mode

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	ed main) Mode	Unit
			MIN.	MAX.	
Transfer rate				fмск/12	bps
		Maximum transfer rate theoretical value fclk = 20 MHz, fмck = fclk		1.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register 4 (SPS4).)



3.5.2 Serial interface IICA

(1) I²C standard mode

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode: fcLκ≥ 1 MHz	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		μS
Hold time ^{Note 1}	thd:STA		4.0		μS
Hold time when SCLA0 = "L"	tLOW		4.7		μS
Hold time when SCLA0 = "H"	tніgн		4.0		μS
Data setup time (reception)	tsu:dat		250		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	μS
Setup time of stop condition	tsu:sto		4.0		μS
Bus-free time	t BUF		4.7		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

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Standard mode: $C_b = 400 \text{ pF}$, $R_b = 2.7 \text{ k}\Omega$



(2) I²C fast mode

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLA0 clock frequency	fscL	fast mode: fcLκ≥ 3.5 MHz	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		μS
Hold time ^{Note 1}	thd:sta		0.6		μS
Hold time when SCLA0 = "L"	tLOW		1.3		μS
Hold time when SCLA0 = "H"	t HIGH		0.6		μS
Data setup time (reception)	tsu:dat		100		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	0.9	μS
Setup time of stop condition	tsu:sto		0.6		μS
Bus-free time	tBUF		1.3		μS

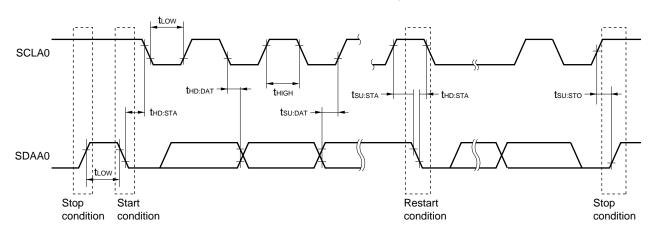
Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



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3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
Input channel	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI2, ANI4 to ANI7	See 3.6.1 (1).	See 3.6.1 (3).	See 3.6.1 (4).
ANI16 to ANI19	See 3.6.1 (2) .		
Internal reference voltage Temperature sensor output voltage	See 3.6.1 (1).		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +125°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	IS	MIN.	TYP.	MAX.	Unit		
Resolution	RES			8		10	bit		
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			1.2	±3.5	LSB		
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS		
		Target pin: ANI2, ANI4 to ANI7	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	3.4		39	μS		
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS		
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.7 V ≤ VDD ≤ 5.5 V	3.8		39	μs		
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR		
Full-scale errorNotes 1, 2	Ers	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR		
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.5	LSB		
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±1.5	LSB		
Analog input voltage	VAIN	ANI2, ANI4 to ANI7		0		AVREFP	V		
		nternal reference voltage HS (high-speed main) mode)			V				
		Temperature sensor output vo (HS (high-speed main) mode	emperature sensor output voltage			V _{TMPS25} Note 4			

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AVREFP = VDD.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AVREFP = VDD.

4. See 3.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI19

(TA = -40 to +125°C, 2.7 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3				±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target ANI pin : ANI16 to ANI19	$2.7 \text{ V} \le \text{V}_{DD} < 5.5 \text{ V}$	3.4		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.35	%FSR
Full-scale error ^{Notes 1, 2}	E _F s	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} Note 3				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AV _{REFP}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.2\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V}, \text{ Reference voltage (+)} = V_{DD}, \text{ Reference voltage (-)} = V_{SS})$

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit		
Resolution	RES			8		10	bit		
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB		
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS		
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	2.7 V ≤ V _{DD} ≤ 5.5 V	3.4		39	μs		
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs		
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	3.8		39	μs		
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR		
Full-scale errorNotes 1, 2	Ers	10-bit resolution				±0.60	%FSR		
Integral linearity errorNote 1	ILE	10-bit resolution				±4.0	LSB		
Differential linearity error	DLE	10-bit resolution				±2.0	LSB		
Analog input voltage	Vain	ANI0 to ANI2, ANI4 to ANI7	,	0		V _{DD}	V		
		ANI16 to ANI19		0		V _{DD}	V		
		Internal reference voltage (HS (high-speed main) mod	nternal reference voltage HS (high-speed main) mode)		V _{BGR} Note 3				
		Temperature sensor output (HS (high-speed main) mod	emperature sensor output voltage			V _{TMPS25} Note 3			

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

^{2.} This value is indicated as a ratio (%FSR) to the full-scale value.

^{3.} See 3.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VBGRNote 3, Reference voltage (-) = AVREFM Note 4 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution			±2.0	LSB
Differential linearity errorNote 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	Vain		0		V _{BGR} Note 3	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. See 3.6.2 Temperature sensor/internal reference voltage characteristics.
- **4.** When reference voltage (–) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AVREFM.

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AVREFM.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvтмрs	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	tamp		5			μS

3.6.3 Programmable gain amplifier

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le AV_{REFP} = V_{DD} \le 5.5 \text{ V}, V_{SS} = AV_{REFM} = 0 \text{ V})$

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9V _{DD} /	V
							gain	
Gain error ^{Note 1}		4, 8 tim	es				±1	%
		16 time	S				±1.5	%
		32 time	2 times				±2	%
Slew rate ^{Note 1}	SRRPGA	Rising edge	$4.0~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	4, 8 times	4			V/μs
				16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$	4, 8 times	1.8			V/μs
				16, 32 times	0.5			V/μs
	SR _{FPGA}	Falling	$4.0~V \leq V_{DD} \leq 5.5~V$	4, 8 times	3.2			V/μs
		edge		16, 32 times	1.4			V/μs
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$	4, 8 times	1.2			V/μs
				16, 32 times	0.5			V/μs
Operation stabilization wait timeNote 2	t PGA	4, 8 times			5			μS
		16, 32 t	imes		10			μS

Notes 1. When V_{IPGA} = 0.1V_{DD}/gain to 0.9V_{DD}/gain.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.

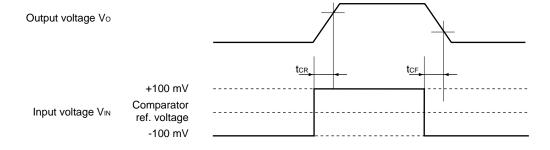
3.6.4 Comparator

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le AV_{REFP} = V_{DD} \le 5.5 \text{ V}, V_{SS} = AV_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		V _{DD}	٧
		СМРСОМ	0.045		0.9V _{DD}	V
Internal reference voltage deviation	△VIREF	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcr	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait timeNote 1	tcmp	$3.3~V \leq V_{DD} \leq 5.5~V$	1			μs
		2.7 V ≤ V _{DD} < 3.3 V	3			μs
Reference voltage stabilization wait time	tvr	CVRE: 0 to 1 ^{Note 2}	10			μS

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - 2. Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.

Remark These characteristics apply when AV_{REFP} is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AV_{REFM} is selected as GND of the internal reference voltage by using the CVRVS1 bit.

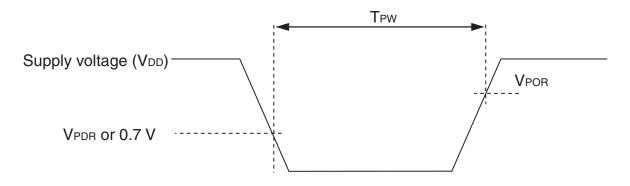


3.6.5 POR circuit characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	Power supply rise time	1.45	1.51	1.62	V
	V _{PDR}	Power supply fall time	1.44	1.50	1.61	V
Minimum pulse width ^{Note}	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _{LVD0}	Power supply rise time	3.97	4.06	4.25	V
voltage			Power supply fall time	3.89	3.98	4.15	V
	V _{LVD1}	Power supply rise time	3.67	3.75	3.93	V	
			Power supply fall time	3.59	3.67	3.83	V
		V _{LVD2}	Power supply rise time	3.06	3.13	3.28	V
		Power supply fall time	2.99	3.06	3.20	V	
		V _{LVD3}	Power supply rise time	2.95	3.02	3.17	V
			Power supply fall time	2.89	2.96	3.09	V
		V _{LVD4}	Power supply rise time	2.85	2.92	3.07	V
			Power supply fall time	2.79	2.86	2.99	V
		V _{LVD5}	Power supply rise time	2.75	2.81	2.95	V
			Power supply fall time	2.70	2.75	2.88	V
Minimum pu	ulse width	tuw		300			μS
Detection de	elay time					300	μS

LVD Detection Voltage of Interrupt & Reset Mode

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol		Cond	litions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _{LVD0}	V _{POC2} ,	C2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage: 2.7 V			2.75	2.88	V
mode	V _{LVD1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.85	2.92	3.07	V
				Falling interrupt voltage	2.79	2.86	2.99	V
	V _{LVD2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.17	V
				Falling interrupt voltage	2.89	2.96	3.09	V
	V _{LVD3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.97	4.06	4.25	V
				Falling interrupt voltage	3.89	3.98	4.15	V

3.6.7 Supply voltage rise inclination characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SV _{DD}				54	V/ms

Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 33.4 AC Characteristics.

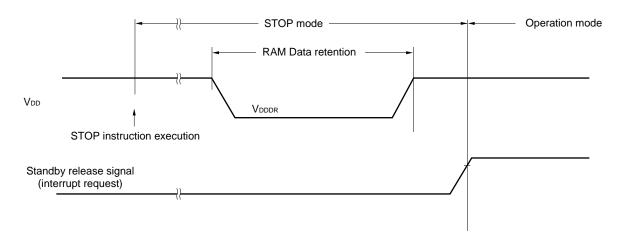
3.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltageNote 2	VDDDR		1.47 ^{Note 1}		5.5	٧

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.

Caution When CPU is operated at the voltage of out of the operation voltage range, RAM data is not retained. Therefore, set STOP mode before the supplied voltage is below the operation voltage range.



3.8 Flash Memory Programming Characteristics

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$2.7~V \leq V_{DD} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years, T _A = 85°C ^{Note 3, 4}	1,000			Times
Number of data flash		Retained for 1 year, T _A = 25°C ^{Note 3, 4}		1,000,000		
rewrites ^{Notes 1, 2, 3}		Retained for 5 years, T _A = 85°C ^{Note 3, 4}	100,000			
		Retained for 20 years, T _A = 85°C ^{Note 3, 4}	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- **4.** These are the average temperature of during the retainment.

3.9 Dedicated Flash Memory Programmer Communication (UART)

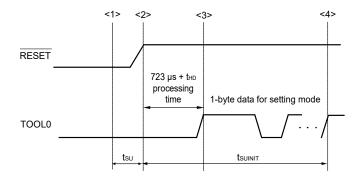
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps

3.10 Timing of Entry to Flash Memory Programming Modes

(Ta = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tно	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Complete the baud rate setting by UART reception.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until an external reset ends

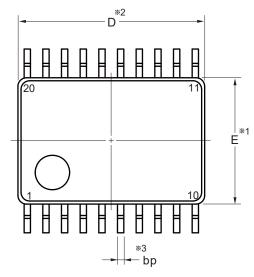
thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

4. PACKAGE DRAWINGS

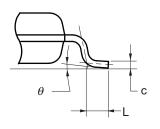
4.1 20-pin Products

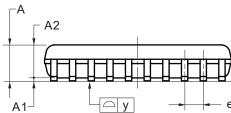
R5F1076CGSP#V0, R5F1076CGSP#X0, R5F1076CMSP#V0, R5F1076CMSP#X0

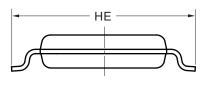
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1











NOTE

- 1.Dimensions "X1" and "X2" do not include mold flash.
- 2.Dimension "X3" does not include trim offset.

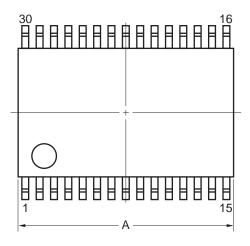
	(UNIT:mm)
ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
Α	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	$0.22 + 0.10 \\ -0.05$
С	$0.15 \pm 0.05 \\ -0.02$
L	0.50±0.20
У	0.10
θ	0° to 10°

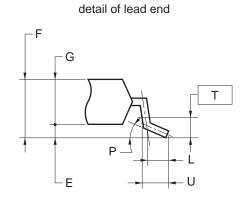
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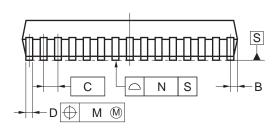
4.2 30-pin Products

R5F107ACGSP#V0, R5F107AEGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#X0, R5F107ACMSP#V0, R5F107AEMSP#V0, R5F107ACMSP#X0, R5F107AEMSP#X0

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

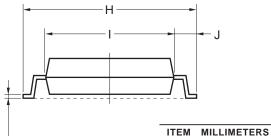






NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.



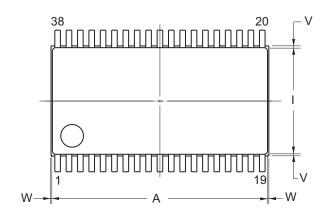
I I E IVI	MILLIMETERS
Α	9.85±0.15
В	0.45 MAX.
С	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
Е	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
- 1	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
М	0.13
N	0.10
Р	3°+5°
Т	0.25
U	0.6±0.15
	•

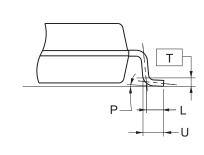
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4.3 38-pin Products

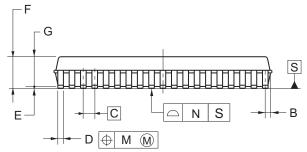
R5F107DEGSP#V0, R5F107DEGSP#X0, R5F107DEMSP#V0, R5F107DEMSP#X0

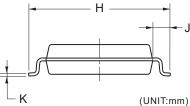
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-SSOP38-0300-0.65	PRSP0038JA-A	P38MC-65-2A4-2	0.3





detail of lead end





NOTE

Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

	(UNIT.IIIII)
ITEM	DIMENSIONS
Α	12.30±0.10
В	0.30
С	0.65 (T.P.)
D	$0.32^{+0.08}_{-0.07}$
Ε	0.125±0.075
F	2.00 MAX.
G	1.70±0.10
Н	8.10±0.20
- 1	6.10±0.10
J	1.00±0.20
K	$0.17^{+0.08}_{-0.07}$
L	0.50
М	0.10
N	0.10
Р	3°+7°
T	0.25(T.P.)
U	0.60±0.15
V	0.25 MAX.
W	0.15 MAX.

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RL78/I1A Datasheet

			Description
Rev.	Date	Page	Summary
3.20	Sep 29, 2017	p.1	Modification of description in 1.1 Features
		p.59	Modification of figure in 2.10 Timing of Entry to Flash Memory Programming Modes
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General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

- 1. Precaution against Electrostatic Discharge (ESD)
 - A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.
- 2. Processing at power-on
 - The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.
- 3. Input of signal during power-off state
 - Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.
- 4. Handling of unused pins
 - Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.
- 5. Clock signals
 - After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.
- 6. Voltage application waveform at input pin
 - Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).
- 7. Prohibition of access to reserved addresses
 - Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.
- 8. Differences between products
 - Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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